

IN THE CLAIMS:

Please amend claim 14 as follows.

14. (Amended) A method of manufacturing a semiconductor device, the method comprising:

depositing a layer of dielectric material, having an as-deposited dielectric constant no greater than about 3, over a conductive region or conductive feature;

forming a photoresist mask on the layer of dielectric material;

forming a through-hole in the dielectric layer exposing the upper surface of the conductive region or conductive feature; and

removing the photoresist mask and cleaning the through-hole with a plasma containing carbon tetrafluoride (CF₄) and water vapor (H₂O) such that the dielectric constant of the dielectric layer does not increase more than about 15%.

REMARKS

Claims 1 through 3, 5 through and 16 through 20 are pending in this application. The specification has been amended consistent with the Examiner's suggestion. In addition, claim 4 has been amended to provide antecedent bases for the photoresist mask as observed by the Examiner. Applicants submit that the present Amendment does not generate any new matter issue.

A clean copy of the paragraphs of the specification affected by the present Amendment and of amended claim 14 appears in the Appendix hereto.

Claim 14 was rejected the second paragraph of 35 U.S.C. §112.